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# 2SK1775

Silicon N-Channel MOS FET

# HITACHI

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## Application

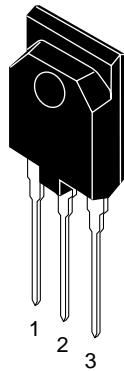
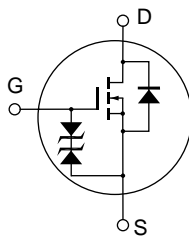
High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter

## Outline

TO-3PFM



1. Gate
2. Drain
3. Source

**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

<b>Item</b>	<b>Symbol</b>	<b>Ratings</b>	<b>Unit</b>
Drain to source voltage	$V_{DSS}$	900	V
Gate to source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	$I_D$	8	A
Drain peak current	$I_{D(pulse)}^{*1}$	20	A
Body to drain diode reverse drain current	$I_{DR}$	8	A
Channel dissipation	$P_{ch}^{*2}$	60	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

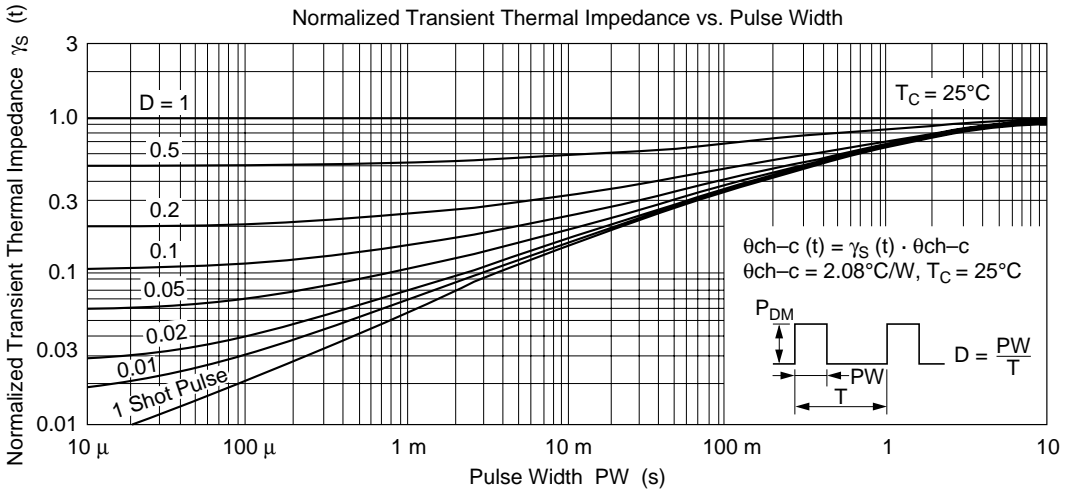
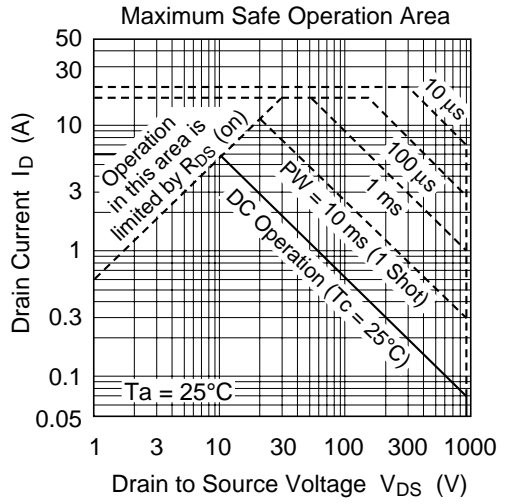
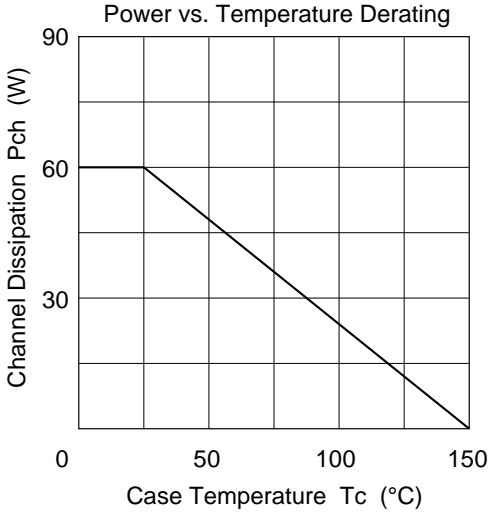
Notes 1.  $PW = 10 \mu s$ , duty cycle 1 %  
2. Value at  $T_c = 25^\circ\text{C}$

## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	900	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 30$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	$\mu\text{A}$	$V_{DS} = 720 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.2	1.6		$I_D = 4 \text{ A}$ $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.5	5.5	—	S	$I_D = 4 \text{ A}$ $V_{DS} = 20 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	1730	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	$C_{oss}$	—	700	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	310	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	25	—	ns	$I_D = 4 \text{ A}$
Rise time	$t_r$	—	135	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	185	—	ns	$R_L = 7.5$
Fall time	$t_f$	—	130	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	0.9	—	V	$I_F = 8 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	900	—	ns	$I_F = 8 \text{ A}, V_{GS} = 0,$ $di_F / dt = 100 \text{ A} / \mu\text{s}$

Note 1. Pulse Test

See characteristic curves of 2SK1342



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# HITACHI

## Hitachi, Ltd.

Semiconductor & IC Div.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan  
Tel: Tokyo (03) 3270-2111  
Fax: (03) 3270-5109

### For further information write to:

Hitachi America, Ltd.  
Semiconductor & IC Div.  
2000 Sierra Point Parkway  
Brisbane, CA. 94005-1835  
U S A  
Tel: 415-589-8300  
Fax: 415-583-4207

Hitachi Europe GmbH  
Electronic Components Group  
Continental Europe  
Dornacher Straße 3  
D-85622 Feldkirchen  
München  
Tel: 089-9 91 80-0  
Fax: 089-9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Div.  
Northern Europe Headquarters  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA  
United Kingdom  
Tel: 0628-585000  
Fax: 0628-778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 0104  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.  
Unit 706, North Tower,  
World Finance Centre,  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon  
Hong Kong  
Tel: 27359218  
Fax: 27306071